

DOCKET NO: 250051US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
MITSUHIRO NOGUCHI, ET AL. : ATTN: APPLICATION DIVISION  
SERIAL NO: NEW U.S. APPLN. :  
FILED: HEREWITH :  
FOR: DATA WRITING METHOD FOR :  
SEMICONDUCTOR MEMORY :  
DEVICE AND SEMICONDUCTOR :  
MEMORY DEVICE

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 4 of this paper.

**Remarks/Arguments** begin on page 8 of this paper.